

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Volker Haerle
Serial No. : Unassigned
Filed : June 6, 2003
Title : METHOD OF PRODUCTION OF SEMICONDUCTOR COMPONENTS

Art Unit : Unknown
Examiner : Unknown

MAIL STOP PATENT APPLICATION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450


INFORMATION DISCLOSURE STATEMENT

Copies of the references listed on the attached form PTO-1449 are enclosed.

This statement is being filed with the application. Please apply any charges or credits to
Deposit Account No. 06-1050.

Respectfully submitted,

Date: 7/22/03



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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12406-059US2	Application No. Unassigned
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Volker Haerle	
		Filing Date Herewith	Group Art Unit Unknown

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	4,415,404	11/15/1983	Riegl			
	AB	4,614,564	09/30/1986	Sheldon et al.			
	AC	4,816,098	03/28/1989	Davis et al.			
	AD	4,980,312	12/25/1990	Harris et al.			
	AE	5,268,069	12/07/1993	Chapple-Sokol et al.			
	AF	5,418,183	05/23/1995	Joyner et al.			
	AG	5,668,038	09/16/1997	Huang et al.			
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	AI	5,937,273	08/10/1999	Fujii et al.			
	AJ	6,140,247	10/31/2000	Muraoka et al.			

Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AK	0746011	10/2001	EP				
	AL	0681315	06/2000	EP				
	AM	02-046407	02/1990	JP				
	AN	07202317	08/1995	JP				
	AO	01270287	10/1989	JP with English Abstract			X	

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
	AP	JP-61 210687 Patent Abstracts of Japan, Venoffentlichung, September 8, 1986
	AQ	G.B., Burns, "Lo-Temperature Native Oxide Removal From Silicon Using Nitrogen Trifluoride Prior To Low-Temperature Silicon Epitaxy", Appl. Phys. Lett. 53 (15), October 1988 pp 1423-1425
	AR	T. Aoyama et al. "Silicon Surface Cleaning Using Photo excited Fluorine Gas Diluted With Hydrogen", J. Electrochem. Soc. Vol. 140, No. 6, June 1993 pp 1704-1708
	AS	K. Ozasa et al., "Deposition Of Thin Indium Oxide Film and Its Application To Selective Epitaxy For In Situ Processing" Thin Solid Films, BD. 246, NR. 1/02, 1994, S. 58-64, XP000453839
	AT	J.P. Harbison et al., "Tungsten Patterning As A Technique For Selective Area III-V MBE Growth", J. Vac. Sci. Technol. B3(2) March/April 1995

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
	AU	JP 02-046407, Patent Abstracts of Japan, Veröffentlichung: February 2, 1990, Anmeldung: August 5, 1988
	AV	S. Yoshida et al., "Selective-Area Epitaxy Of GaAs Using A New Mask Material For In Situ Processes", Inst. Phys. Conf. Ser. No. 129: Chapter 3, 1992, S-49-54, XP000366199
	AW	P.J. Sullivan, et al., "Selective-Area Epitaxy For GaAs-on-InP Optoelectronic Integrated Circuits (OEICs)", Semiconductor Sci. & Technol. 8, No. 6, June 1993, pp 1179-1185
	AX	Whidden T.K. et al.; "Catalyzed HF Vapor Etching Of Silicon Dioxide Für Micro-and Nanolithographic Masks"; April 1995; J. Electrochem Soc., Vol. 142, No. 4, pp 1199-1204
	AY	Torek K. et al.; "Reduced Pressure Etching Of Thermal Oxides In Anhydrous HF/Alcoholic Gas Mixtures"; April 1995; J. Electrochem Soc., Vol. 142, No. 4, pp 1322-1326
	AZ	Wong M. et al., "Characterization Of Wafer Cleaning And Oxide And Oxide Etching Using Vapor-Phase Hydrogen Fluoride"; June 1991, J. Electrochem, Soc., Vol. 138, No. 6, pp 1799-1802

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